

Title (en)

METHOD FOR MAKING AN ANISOTROPIC CONDUCTIVE POLYMER FILM ON A SEMICONDUCTOR WAFER

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES ANISOTROPISCHEN ELEKTRISCH-LEITENDEN POLYMERFILMS AUF EINE HALBLEITERSCHEIBE

Title (fr)

PROCEDE DE FABRICATION DE FILM POLYMERE CONDUCTEUR ANISOTROPE SUR TRANCHE DE SEMI-CONDUCTEUR

Publication

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Application

EP 03748222 A 20030722

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- FR 0209378 A 20020724

Abstract (en)

[origin: WO2004012226A2] The invention concerns a method for making an anisotropic conductive polymer film (23, 24) on a semiconductor wafer (T) comprising, on one face, a passivation layer (12) wherein is provided at least one opening exposing a bond pad (11). The invention is useful for forming components (chips, integrated circuits) with high interconnect density.

IPC 1-7

H01L 21/00

IPC 8 full level

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CPC (source: EP US)

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